

## N-Channel 200 V (D-S) MOSFET

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ) (Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
200	7 at V <sub>GS</sub> = 10 V	125	89.5 nC

### FEATURES

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- Fast switching
- AEC-Q101 Qualified for Automotive Applications

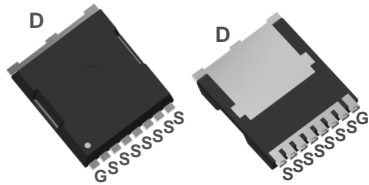


**RoHS**  
COMPLIANT

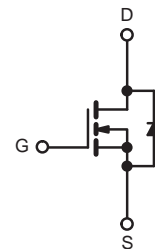
### APPLICATIONS

- Load switch
- Networking
- Quick Charger

### TOLL Pin Configuration



Top View



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	200	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>C</sub> = 25 °C	125	A
		T <sub>C</sub> = 100 °C	105	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	500		
Single Avalanche Energy	E <sub>AS</sub>	1020	mJ	
Maximum Power Dissipation <sup>c</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	483	W
		T <sub>C</sub> = 100 °C	241	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +175	°C	

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	45	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.31	

### Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.
- The value of R<sub>thJA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25 °C.

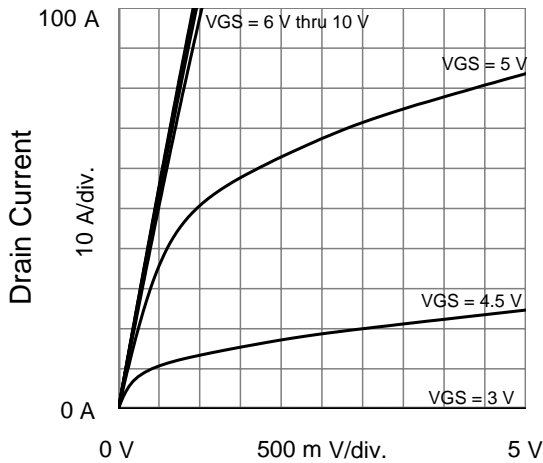
SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$	-	-	100	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	120	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	-	7	9	m $\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 5\text{ V}, I_D = 20\text{ A}$	-	51	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	5890	-	pF
Output Capacitance	$C_{oss}$		-	442	-	
Reverse Transfer Capacitance	$C_{rss}$		-	13	-	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	-	89.5	-	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$		-	19.6	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	21.8	-	
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	-	2.5	-	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 100\text{ V}, I_D = 20\text{ A}, R_g = 3\text{ }\Omega$ $V_{GS} = 10\text{ V}$	-	20	-	ns
Rise Time <sup>c</sup>	$t_r$		-	22	-	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$		-	42	-	
Fall Time <sup>c</sup>	$t_f$		-	26	-	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (<math>T_C = 25\text{ }^\circ\text{C}</math>)</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	125	A
Pulsed Current	$I_{SM}$		-	-	500	A
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 1\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	102	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	690	-	nC

**Notes**

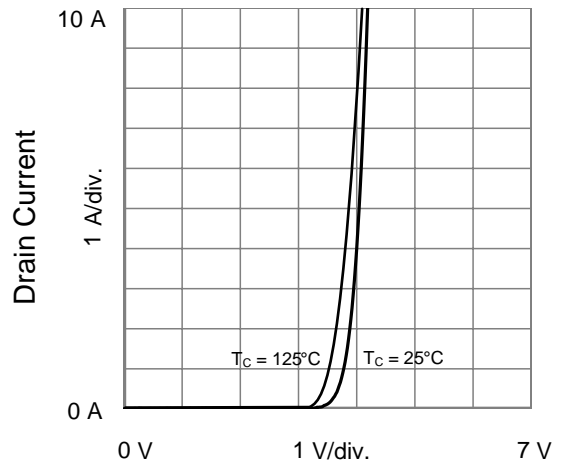
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

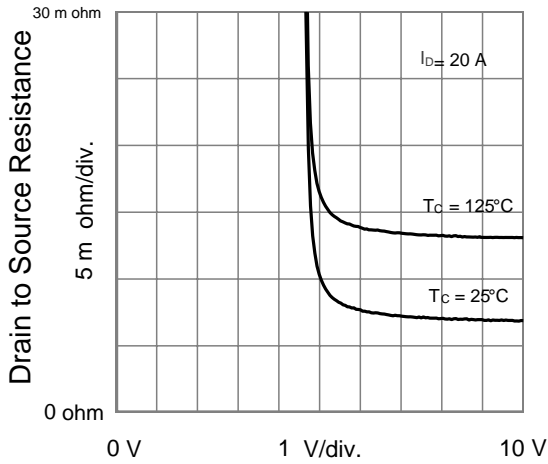
**TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)**



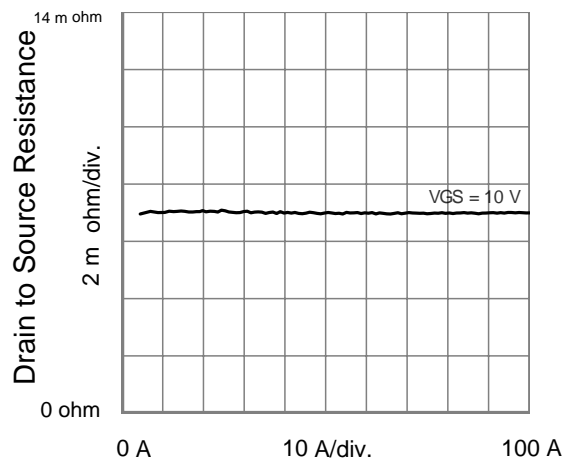
**Drain to Source Voltage Output Characteristics**



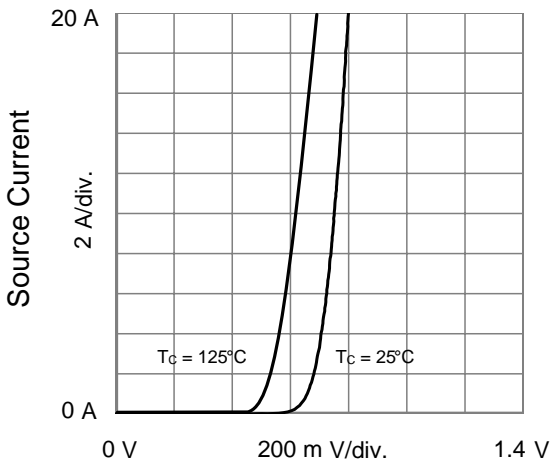
**Gate to Source Voltage Transfer Characteristics**



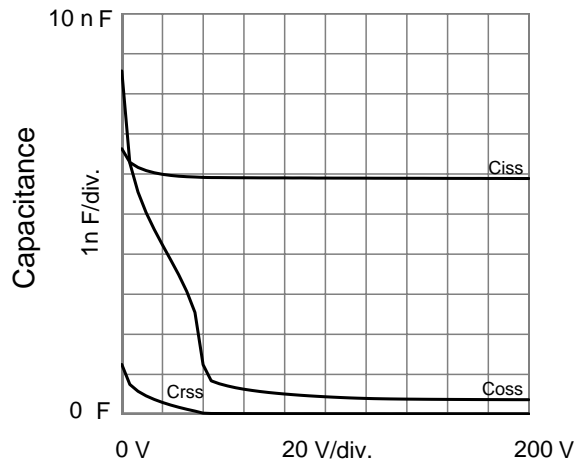
**Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltage**



**Drain Current**

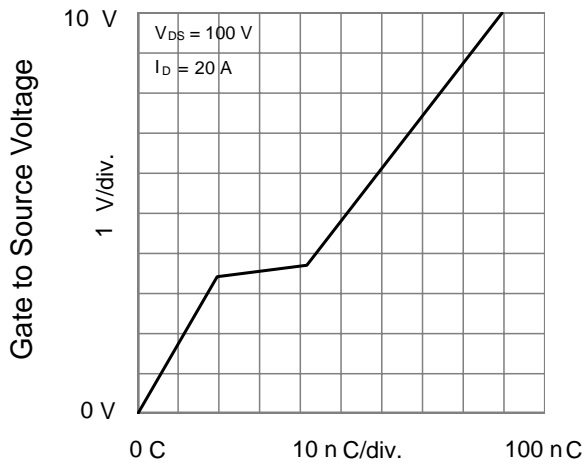


**Source to Drain Voltage Body Diode Forward Characteristics**

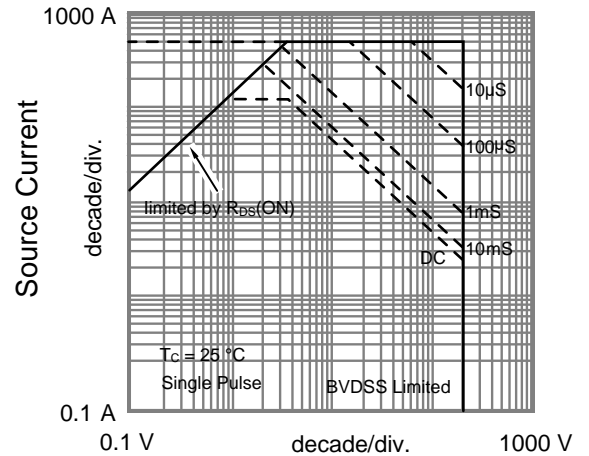


**Drain to Source Voltage Capacitances**

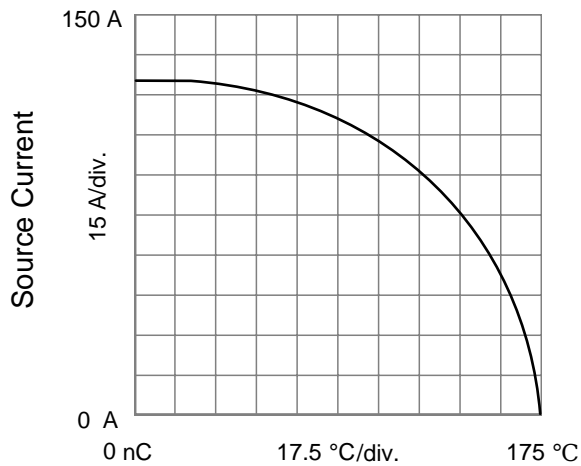
**TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**



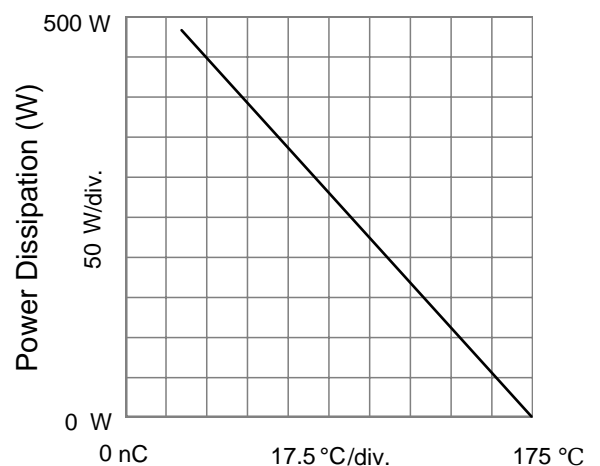
**Gate Charge**  
Gate to Source Voltage vs. Gate Charge



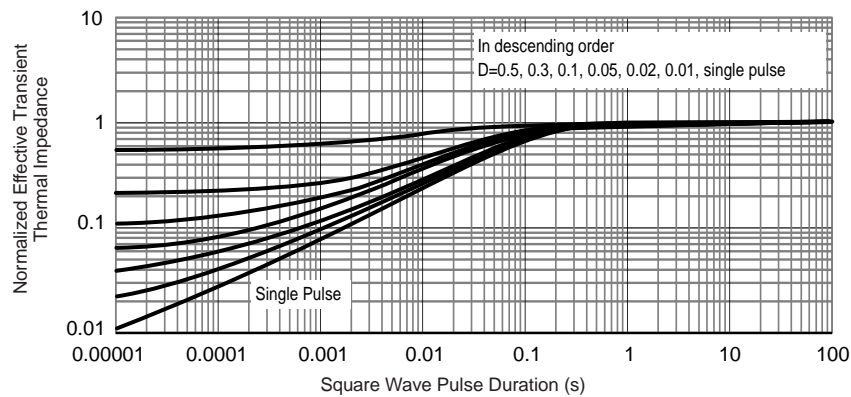
**Source to Drain Voltage**  
Safe Operating Area, Junction-to-Case



**T<sub>C</sub> - Case Temperature**

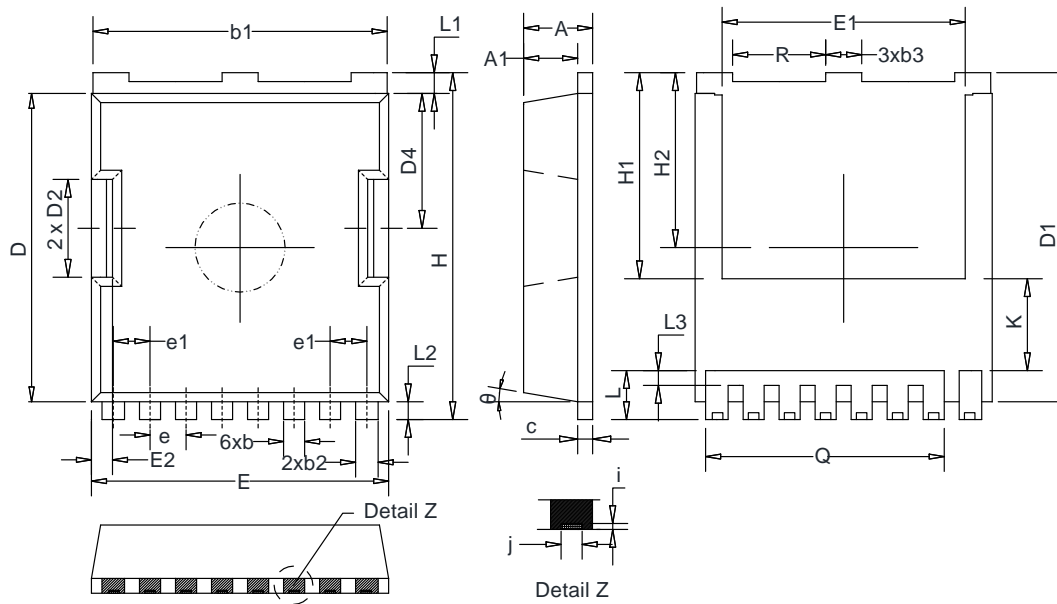


**T<sub>C</sub> - Case Temperature**



**Normalized Thermal Transient Impedance, Junction-to-Case**

**TOLL PACKAGE OUTLINE**



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.05	2.30	2.65	E2	0.40	0.70	0.90
A1	1.50	1.80	2.10	H	11.30	11.70	12.10
b	0.50	0.70	0.90	H1	6.95 BSC		
$b_1$	9.50	9.80	10.05	H2	5.90 BSC		
$b_2$	0.50	0.75	1.00	i	0.10 REF		
$b_3$	1.00	1.20	1.45	j	0.35 REF		
c	0.30	0.50	0.75	K	3.10 REF		
D	10.10	10.40	10.70	L	1.45	1.65	1.85
$D_1$	10.80	11.10	11.40	L1	0.50	0.70	0.90
$D_2$	3.10	3.30	3.50	L2	0.40	0.60	0.80
$D_4$	4.35	4.55	4.80	L3	0.30	0.50	0.70
e	1.20 BSC			Q	7.95 REF		
$e_1$	1.225 BSC			R	2.80	3.10	3.35
E	9.65	9.90	10.15	$\theta$	10°REF		
$E_1$	7.80	8.10	8.50				

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